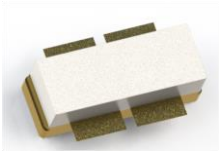
XTAH58150F4C GaN TRANSISTOR

Document Number: XTAH58150F4C
Advanced Datasheet V1.0

Gallium Nitride 28V 150W, C band RF Power Transistor

XTAH58150F4C



Description

The XTAH58150F4C is a 150W internally matched, GaN HEMT, designed from 5.0 to 6.0GHz, especially 5G NR or LTE application, as well as either Pulse or CW application

There is no guarantee of performance when this part is used in applications designed Outside of these frequencies.

- Typical **CW** performance (on 5.7-5.9GHz fixture with device soldered)：

Vds=28V, I_{DQ}=300mA, Tc=25 °C

Freq(MHz)	Pin(dBm)	Pout(dBm)	Pout(W)	IDS(A)	Gain(dB)	Eff(%)
5700	42.2	51.91	155.24	11.95	9.71	46.40
5800	41.6	52.1	162.18	11.9	10.5	48.67
5900	41.8	52	158.49	10.95	10.2	51.69

Vds=32V, I_{DQ}=300mA, Tc=25 °C

Freq(MHz)	Pin(dBm)	Pout(dBm)	Pout(W)	IDS(A)	Gain(dB)	Eff(%)
5700	43.5	52.82	191.43	13	9.32	46.02
5800	42.2	52.84	192.31	12.64	10.64	47.54
5900	42.5	52.8	190.55	11.82	10.3	50.38

Recommended driver：GTAH58025GX

Applications and Features

- Suitable for wireless communication infrastructure, wideband amplifier, EMC testing, ISM etc.
- High Efficiency and Linear Gain Operations
- Thermally Enhanced Industry Standard Package
- High Reliability Metallization Process
- Excellent thermal Stability and Excellent Ruggedness
- Compliant to Restriction of Hazardous Substances (RoHS) Directive 2002/95/EC

Important Note: Proper Biasing Sequence for GaN HEMT Transistors

Turning the device ON

1. Set VGS to the pinch--off (VP) voltage, typically –5 V
2. Turn on VDS to nominal supply voltage (28V)
3. Increase VGS until IDS current is attained
4. Apply RF input power to desired level

Turning the device OFF

1. Turn RF power off
2. Reduce VGS down to VP, typically –5 V
3. Reduce VDS down to 0 V
4. Turn off VGS

Figure 1: Pin definitions (Top view)

Because of internal configuration, it must be used as single ended device.

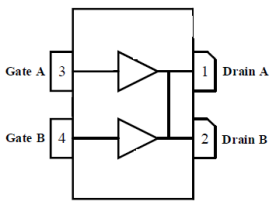


Table 1. Maximum Ratings

Rating	Symbol	Value	Unit
Drain--Source Voltage	V_{DSS}	150	Vdc
Gate--Source Voltage	V_{GS}	-10,+2	Vdc
Operating Voltage	V_{DD}	36	Vdc
Maximum Forward Gate Current @ TC = 25°C	Igmax	33.6	mA
Storage Temperature Range	Tstg	-65 to +150	°C
Case Operating Temperature	T_C	+150	°C
Operating Junction Temperature(See note 1)	T_J	+225	°C
Total Device Power Dissipation (Derated above 25°C, see note 2)	Pdiss	260	W

Note: 1. Continuous operation at maximum junction temperature will affect MTTF
2.Bias Conditions should also satisfy the following expression: Pdiss < (Tj – Tc) / RJC and Tc = Tcase

Table 2. Thermal Characteristics

Characteristic	Symbol	Value	Unit
Thermal Resistance, Junction to Case T_C= 85°C, T_J=200°C, RF CW operation	RθJC	0.7	C/W

Table 3. Electrical Characteristics (T_C = 25℃ unless otherwise noted)

DC Characteristics

Characteristic	Conditions	Symbol	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	V_{GS}=-8V; I_{DS}=33.6mA	V_{DSS}	150			V
Gate Threshold Voltage	V_{DS} = 28V, I_D =33.6mA	V_{GS}(th)	-4		-2	V
Gate Quiescent Voltage	V_{DS} =28V, I_{DS}=500mA, Measured in Functional Test	$V_{GS(Q)}$		-2.2		V

Typical performance

5.7-5.9GHz

Figure 2: Small singal gain and return loss Vs Frequency

Vds=28V, Idq=500mA, input power=0dBm

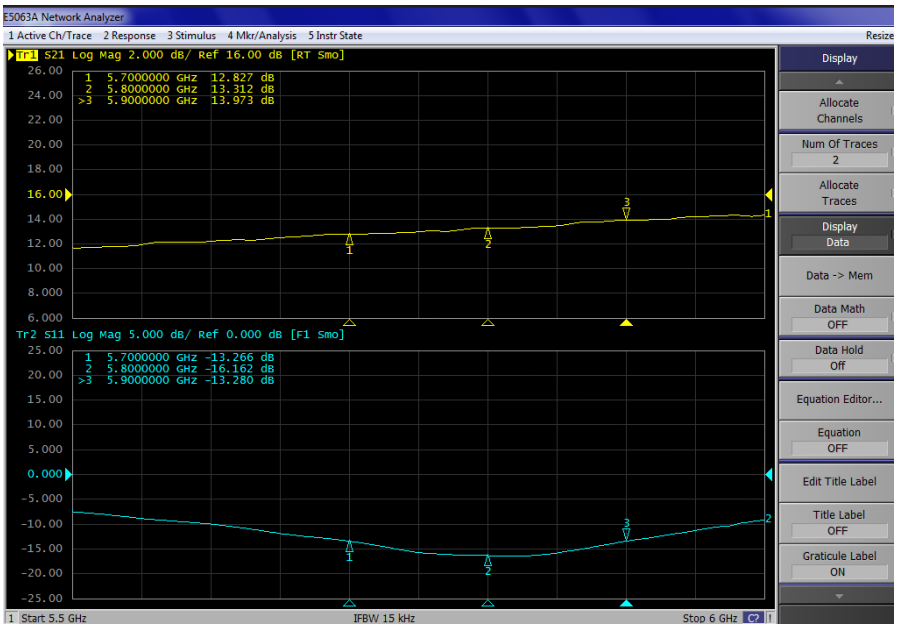
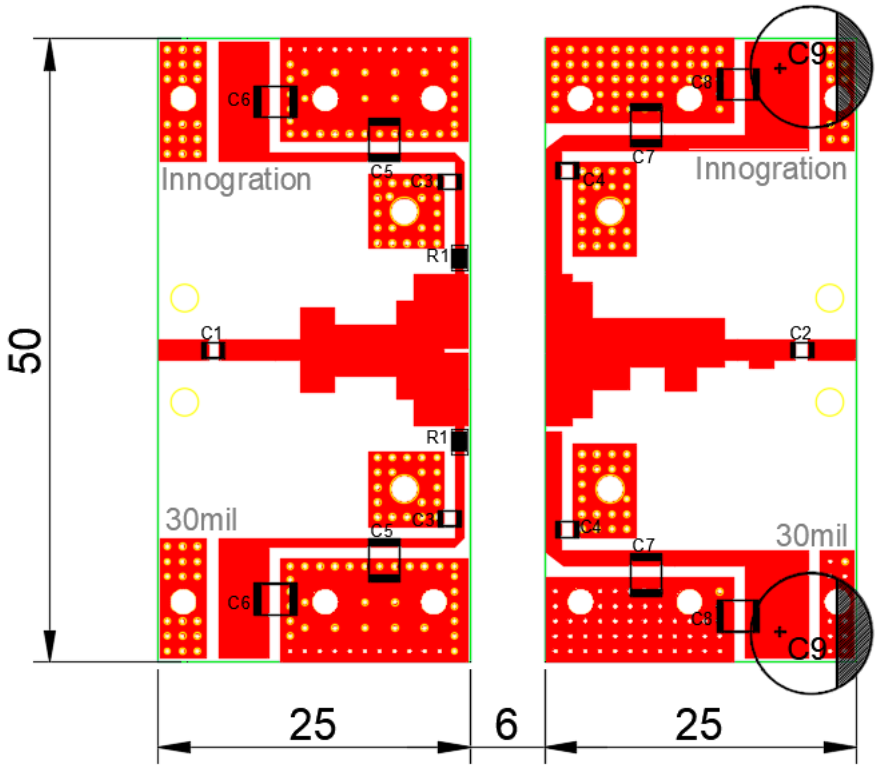


Figure 3: Picture and Bill of materials of 5.7-5.9GHz wide band application circuit

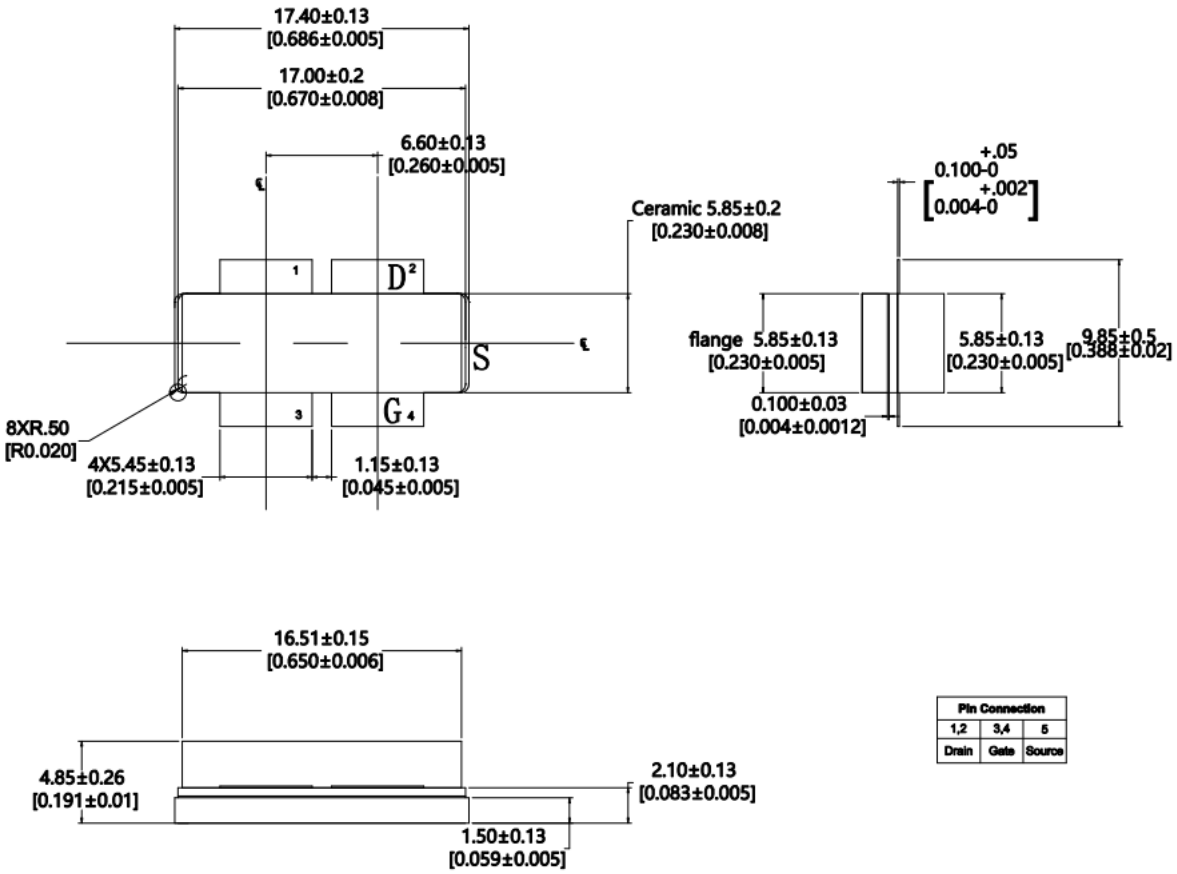
(Layout Gerber file upon request)



Component	Description	Suggestion
C9	470uF/63V	-
C5,C6,C7,C8	10uF/1210	-
C2	3.9pF/ MQ301111	BEIJING YUANLU HONGYUAN ELECTRONIC TECHNOLOGY CO., LTD.
C1、C3、C4	3.9pF/ MQ300805	BEIJING YUANLU HONGYUAN ELECTRONIC TECHNOLOGY CO., LTD.
R1	Chip Resistor ,10Ω/0805	-
PCB	30mil / Rogers 4350 30mil	-

Package Outline

Flangeless ceramic package; 4 leads



OUTLINE VERSION	REFERENCE			EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA		
PKG-LBS					07/31/2023

Revision history

Table 4. Document revision history

Date	Revision	Datasheet Status
2024/12/4	V1.0	Advanced Datasheet Creation, product unreleased yet

Application data based on YHG-24-28